# **BLF8G27LS-150V**; BLF8G27LS-150GV Power LDMOS transistor

**AMPLEON** 

Rev. 4 — 1 September 2015

Product data sheet

### **Product profile**

#### 1.1 General description

150W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in a common source class-AB production test circuit.

Test signal	f	$I_{Dq}$	V <sub>DS</sub>	$P_{L(AV)}$	Gp	$\eta_{D}$	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2600 to 2700	1300	28	45	18	30	-30 <sup>[1]</sup>

<sup>[1] 3</sup>GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz. Channel bandwidth is 3.84 MHz.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R<sub>th</sub> providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (60 MHz typical)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range

### 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF8G27	'LS-150V (SOT1244B)		
1	drain	4 4 5	4
2	gate	— 4 1 5 ∏	6,7 → 1 → 4,5
3	source [		2
4	decoupling lead	3	3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8G27	LS-150GV (SOT1244C)		
1	drain		
2	gate	4 1 5 	6.7→1 → 4.5
3	source [		6,7
4	decoupling lead		2 - 1 - 7
5	decoupling lead		aaa-003619
6	n.c.	6 2   7	
7	n.c.		

<sup>[1]</sup> Connected to flange.

### 3. Ordering information

Table 3. Ordering information

Type number	Packag	Package			
	Name	me Description			
BLF8G27LS-150V	-	earless flanged ceramic package; 6 leads	SOT1244B		
BLF8G27LS-150GV	-	earless flanged ceramic package; 6 leads	SOT1244C		

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		<u>[1]</u> _	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 45 W	0.30	K/W

#### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 216 mA	1.5	1.9	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	4.5	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	40	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 11 V; $V_{DS}$ = 0 V	-	-	450	nΑ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 10.8 A	-	16	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 7.56 A$	-	0.06	-	Ω

#### Table 7. RF characteristics

Test signal: 2-carrier W-CDMA, 3GPP test model; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF, carrier spacing 5 MHz;  $f_1$  = 2602.5 MHz;  $f_2$  = 2607.5 MHz;  $f_3$  = 2692.5 MHz;  $f_4$  = 2697.5 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 45 \text{ W}$	16.8	18	-	dB
RLin	input return loss	$P_{L(AV)} = 45 \text{ W}$	-	-10	-7	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 45 \text{ W}$	26	30	-	%
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)	P <sub>L(AV)</sub> = 45 W	-	-30	-26	dBc

#### 7. Test information

#### 7.1 Ruggedness in class-AB operation

The BLF8G27LS-150V and BLF8G27LS-150GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 1300 \text{ mA}$ ;  $P_L = 150 \text{ W}$  (CW); f = 2600 MHz.

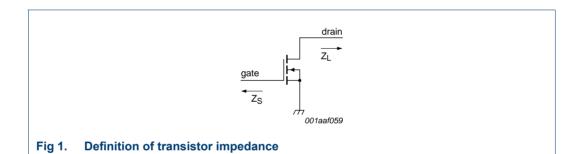
### 7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data;  $I_{Dq} = 1300 \text{ mA}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]
(MHz)	(Ω)	(Ω)
BLF8G27LS-150V		
2500	0.70 - j3.50	2.68 – j1.86
2600	1.10 – j4.40	2.86 – j2.03
2700	2.00 - j4.90	3.27 – j1.87
BLF8G27LS-150GV		
2500	1.00 – j5.70	2.35 – j4.04
2600	1.50 – j6.90	2.52 – j4.32
2700	2.10 – j8.00	3.21 – j4.36

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.



#### 7.3 Test circuit

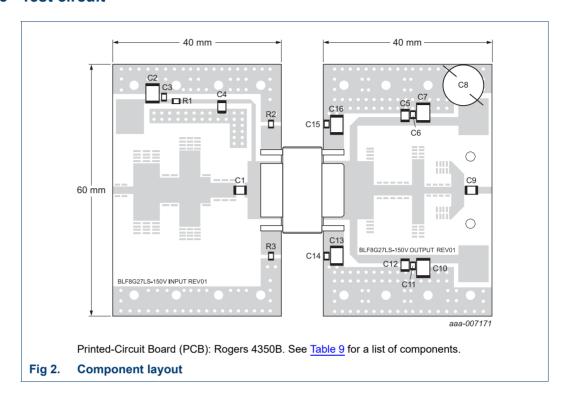


Table 9. List of components

See Figure 2 for component layout.

The used PCB material is Rogers RO4350B with a thickness of 0.76 mm.

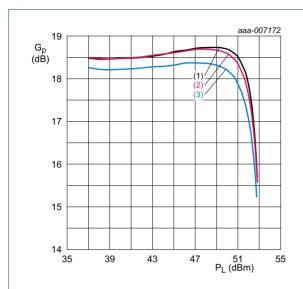
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	0.7 μF	[1] ATC800B
C2	multilayer ceramic chip capacitor	1 μF	[2] Murata
C3	multilayer ceramic chip capacitor	100 nF	[2] Murata
C4, C5, C9, C12	multilayer ceramic chip capacitor	24 pF	11 ATC800B
C6, C11, C14, C15	multilayer ceramic chip capacitor	220 nF	[2] Murata
C7, C10, C13, C16	multilayer ceramic chip capacitor	4.7 μF, 50 V	[2] Murata
C8	electrolytic capacitor	> 470 μF, 63 V	
R1	chip resistor	4.7 $\Omega$ , 1 % tolerance	SMD 1206
R2, R3	chip resistor	0 Ω	SMD 1206

<sup>[1]</sup> American Technical Ceramics type 800B or capacitor of same quality.

<sup>[2]</sup> Murata or capacitor of same quality.

#### 7.4 Graphical data

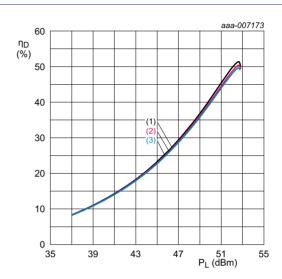
#### 7.4.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $t_p$  = 100  $\mu s; \, \delta$  = 10 %.

- (1) f = 2600 MHz
- (2) f = 2655 MHz
- (3) f = 2700 MHz

Fig 3. Power gain as a function of output power; typical values

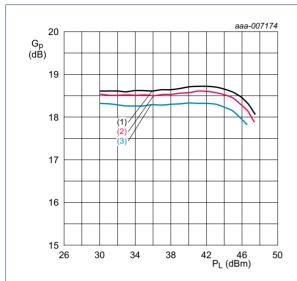


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2600 MHz
- (2) f = 2655 MHz
- (3) f = 2700 MHz

Fig 4. Drain efficiency as a function of out power; typical values

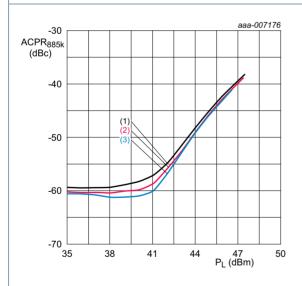
#### 7.4.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

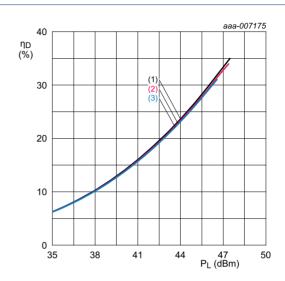
Fig 5. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

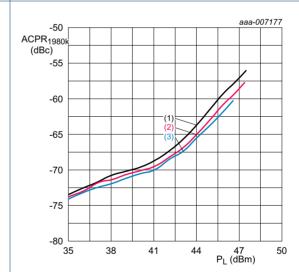
Fig 7. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 6. Drain efficiency as a function of output power; typical values



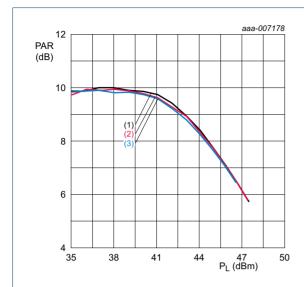
 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 8. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

# BLF8G27LS-150(G)V

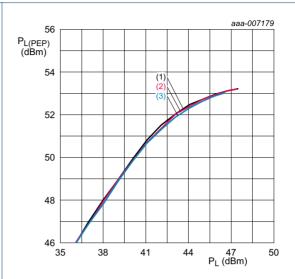
**Power LDMOS transistor** 



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 9. Peak-to-average power ratio as a function of output power; typical values

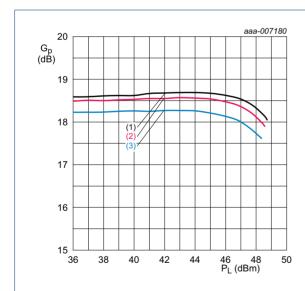


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 10. Peak envelope power load power as a function of output power; typical values

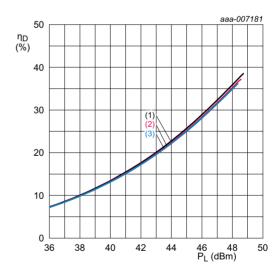
#### 7.4.3 1-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

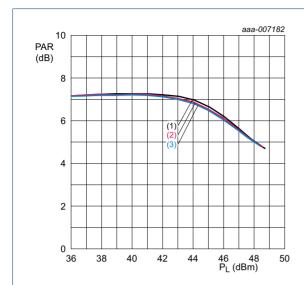
Fig 11. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

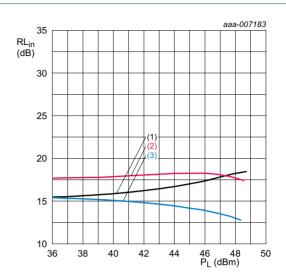
Fig 12. Drain efficiency as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

Fig 13. Peak-to-average power ratio as a function of output power; typical values

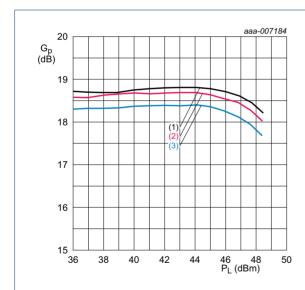


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

Fig 14. Input return loss as a function of output power; typical values

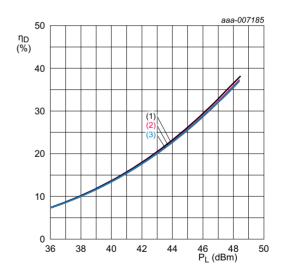
#### 7.4.4 2-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

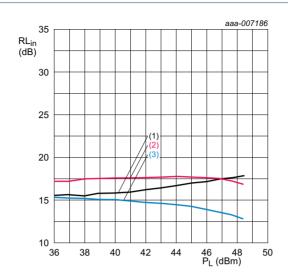
Fig 15. Power gain as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

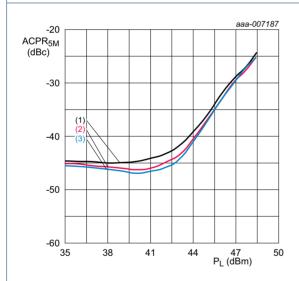
Fig 16. Drain efficiency as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

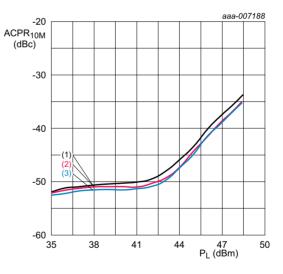
Fig 17. Input return loss as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 18. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

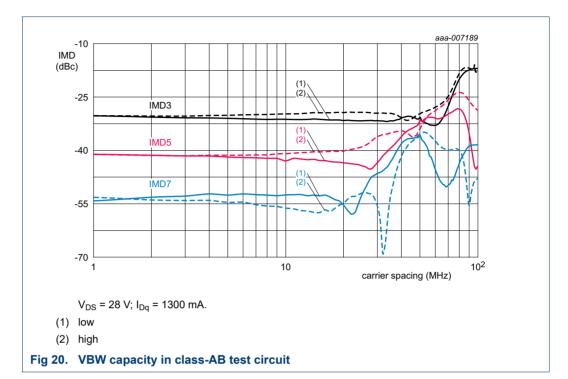


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 19. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

#### 7.4.5 2-Tone VBW



### Package outline

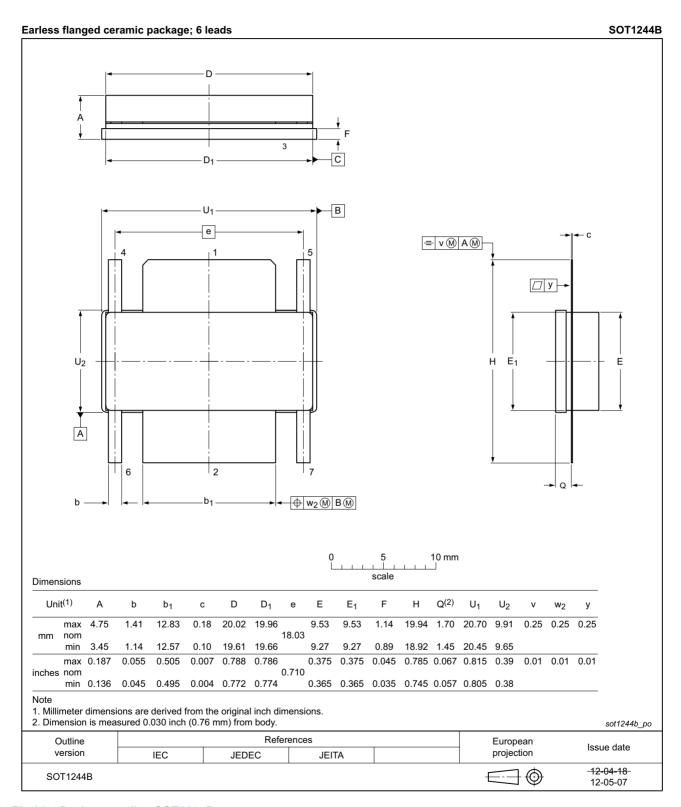


Fig 21. Package outline SOT1244B

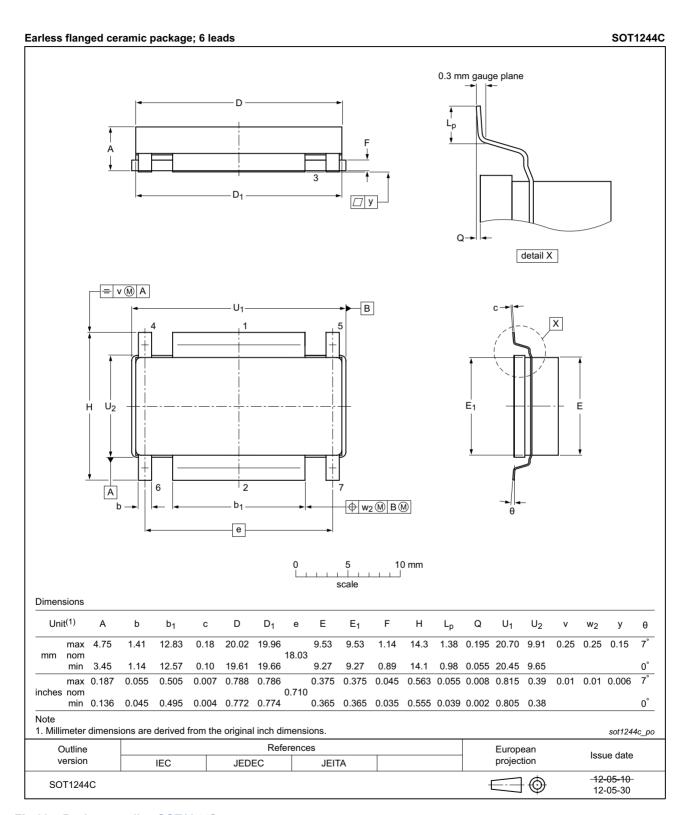


Fig 22. Package outline SOT1244C

### 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

### 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G27LS-150V_8G27LS-150GV#4	20150901	Product data sheet		BLF8G27LS-150V_ 8G27LS-150GV v.3
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>			
BLF8G27LS-150V_8G27LS-150GV v.3	20130626	Product data sheet	-	BLF8G27LS-150V_ 8G27LS-150GV v.2
BLF8G27LS-150V_8G27LS-150GV v.2	20130422	Objective data sheet	-	BLF8G27LS-150V_ 8G27LS-150GV v.1
BLF8G27LS-150V_8G27LS-150GV v.1	20130129	Objective data sheet	-	-

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition		
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.		
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.		
Product [short] data sheet	Production	This document contains the product specification.		

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BLF8G27LS-150V 8G27LS-150GV#4

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## **BLF8G27LS-150(G)V**

**Power LDMOS transistor** 

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### **AMPLEON**

# BLF8G27LS-150(G)V

**Power LDMOS transistor** 

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